

LTVS20H12ET5G

1-Line Uni-directional TVS Diode

The TVS20H12 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The TVS20H12 complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. The high ESD surge protection make TVS20H12 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

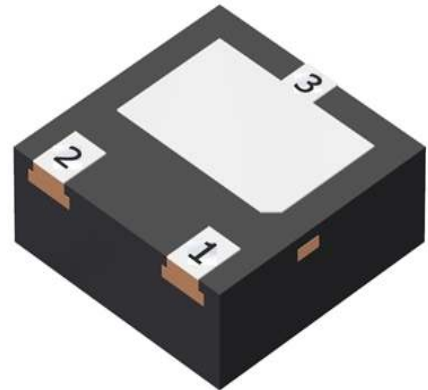
Features

- Protects one data or power line
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
- RoHS Compliant

Applications

- Mobile Phones
- Battery Protection
- Power Line Protection
- Vbat pin for Mobile Devices
- Hand Held Portable Applications

LTVS20H12ET5G



DFN2020-3



Ordering information

| Device | Marking | Shipping |
|---------------|---------|----------------|
| LTVS20H12ET5G | ET | 3000/Tape&Reel |

LTVS20H12ET5G

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|--|--------|-------------|--------------------|
| Peak Pulse Power (8/20 μs) | Ppk | 4000 | W |
| Peak Pulse Current (8/20 μs) | Ipp | 180 | A |
| ESD per IEC 61000-4-2 (Air) | VESD | ± 30 | kV |
| ESD per IEC 61000-4-2 (Contact) | | ± 30 | |
| Operating Temperature Range | TJ | -55 to +125 | $^{\circ}\text{C}$ |
| Storage Temperature Range | Tstg | -55 to +150 | $^{\circ}\text{C}$ |

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
|-------------------------|--------|------|------|------|---------------|---|
| Reverse Working Voltage | VRWM | | | 12 | V | |
| Breakdown Voltage | VBR | 12.8 | 13.8 | 14.5 | V | $I_R = 1\text{mA}$ |
| Reverse Leakage Current | I_R | | | 1 | μA | $V_R = 12\text{V}$ |
| Forward Voltage | V_F | | 0.75 | 1.2 | V | $I_F = 10\text{mA}$ |
| Clamping Voltage | V_C | | | 16.5 | V | $I_{PP} = 50\text{A}$ (8 x 20 μs pulse) |
| Clamping Voltage | V_C | | | 18.8 | V | $I_{PP} = 100\text{A}$ (8 x 20 μs pulse) |
| Clamping Voltage | V_C | | 21 | | V | $I_{PP} = 180\text{A}$ (8 x 20 μs pulse) |
| Junction Capacitance | CJ | | 1450 | 1600 | pF | $V_R = 0\text{V}$, $f = 1\text{MHz}$ |

LTVS20H12ET5G

Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)

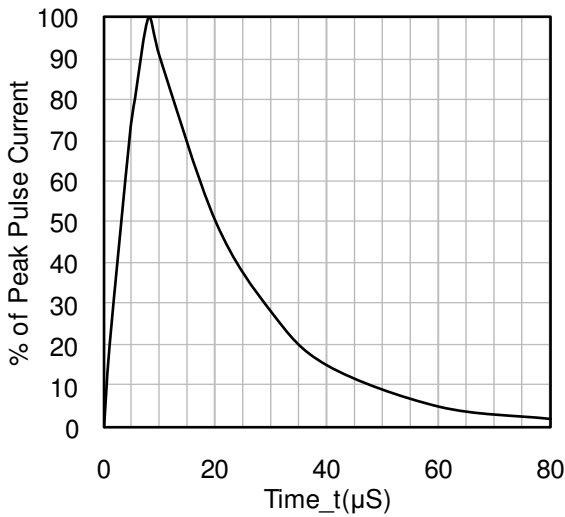


Fig1. (8 x 20µs)Pulse Waveform

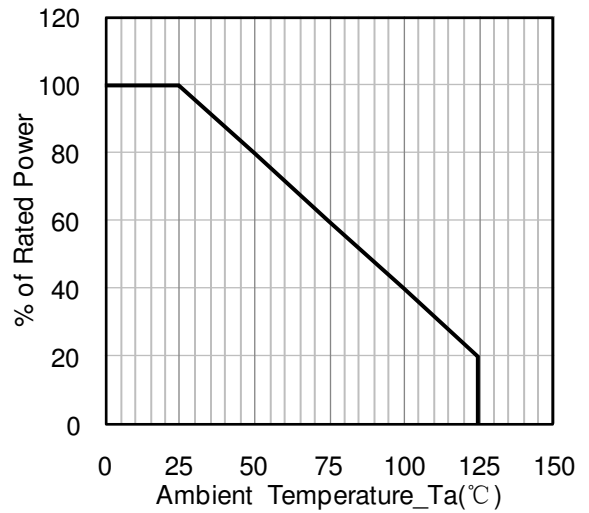


Fig2. Power Derating Curve

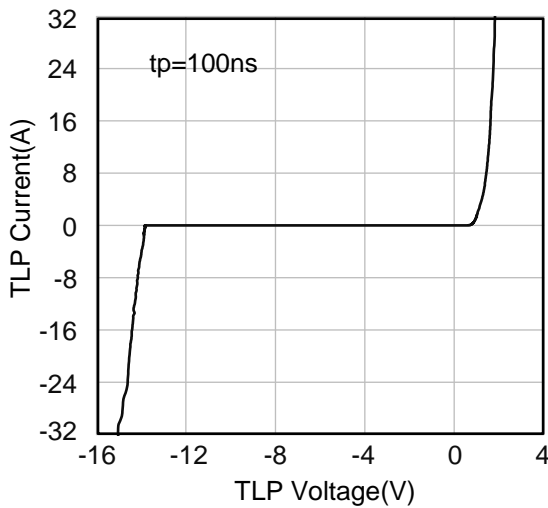


Fig3. TLP Measurement

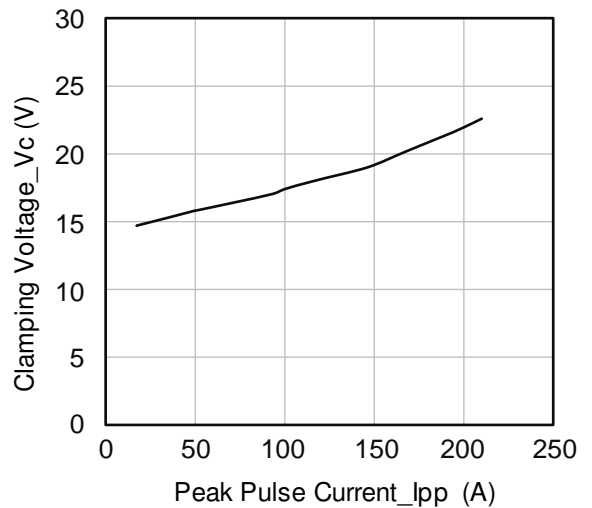
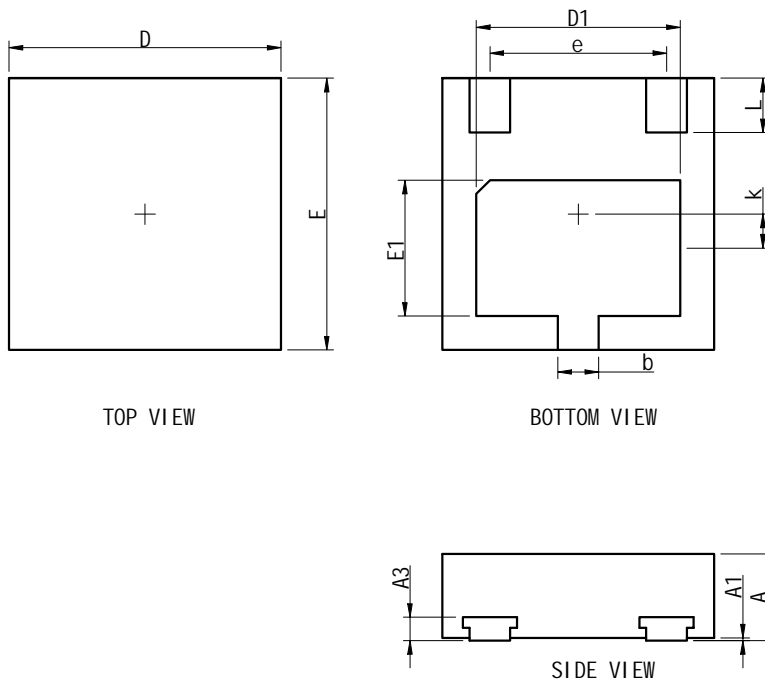


Fig4. Clamping Voltage vs. Peak Pulse Current

LTVS20H12ET5G

Package Outline Dimension

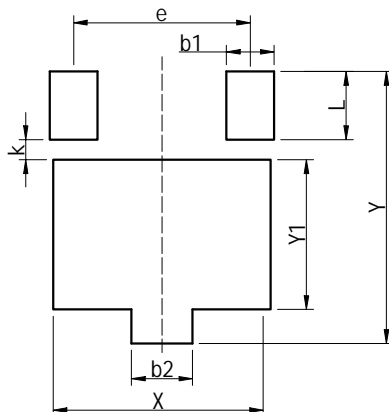
DFN2020-3



| DFN2020-3 | | | |
|-----------|-----------|------|------|
| Dim | Min. | Typ. | Max. |
| A | 0.60 | 0.65 | 0.70 |
| A1 | 0.00 | 0.02 | 0.05 |
| A3 | 0.152REF. | | |
| D | 1.95 | 2.00 | 2.05 |
| E | 1.95 | 2.00 | 2.05 |
| D1 | 1.45 | 1.50 | 1.55 |
| E1 | 0.95 | 1.00 | 1.05 |
| b | 0.25 | 0.30 | 0.35 |
| e | 1.30TYP. | | |
| k | 0.20 | 0.25 | 0.30 |
| L | 0.35 | 0.40 | 0.45 |

All Dimensions in mm

Suggested Pad layout



| DFN2020-3 | |
|-----------|------|
| Dim | (mm) |
| X | 1.60 |
| Y | 2.00 |
| b1 | 0.35 |
| b2 | 0.45 |
| L | 0.50 |
| Y1 | 1.10 |
| k | 0.15 |
| e | 1.30 |

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)

[>>点击查看相关商品](#)